AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A method for fabricating a semiconductor laser device including a plurality of semiconductor laser elements on a sub mount, said method comprising:

an emission source forming step of stacking a semiconductor layer structure on a single substrate and forming a plurality of emission sources on the substrate;

a mounting step of mounting the substrate with the emission sources on the sub mount; and

after the substrate with the emission sources thereon is mounted on the submount, a substrate cutting step of cutting through the substrate between the emission sources, so as to form a plurality of laser elements each including a portion of the substrate and an emission source.

2. (Original) The method as set forth in claim 1, wherein: said emission source forming step further comprises the step of forming isolation grooves in the semiconductor layer structure after forming the emission sources, so as to isolate the emission sources from one another.

3. (Original) The method as set forth in claim 2, wherein the isolation grooves are formed at greater intervals than the substrate.

4. (Original) The method as set forth in claim 3, wherein the isolation grooves taper toward the substrate.

5. (Original) The method as set forth in claim 2, wherein the isolation grooves are formed by etching.

6. (Original) The method as set forth in claim 2, wherein the isolation grooves in the semiconductor layer structure are defined by a specific crystal face of a semiconductor material of the semiconductor layer structure.

7. (Original) The method as set forth in claim 1, wherein the sub mount is an insulator.

8. (Original) The method as set forth in claim 7, wherein the sub mount is made of ceramic.

9. (Original) The method as set forth in claim 1, wherein the sub mount is a semiconductor.

10. (Original) The method as set forth in claim 1, wherein said substrate cutting step is carried out by any one of etching, blade dicing, and stealth dicing.

11-12. (Canceled)

13. (New) The method of claim 1, wherein the substrate is a GaAs substrate.

14. (New) The method of claim 1, wherein the substrate comprises GaAs and may optionally be doped with silicon.